

L Number	Hits	Search Text	DB	Time stamp
1	12040	floating adj gate	USPAT; US-PGPUB	2003/06/23 15:04
2	987	(floating adj gate) SAME thickness same (angstrom nanometer micron nm .mu)	USPAT; US-PGPUB	2003/06/23 15:06
3	714	(floating adj gate) SAME thickness near3 (angstrom nanometer micron nm .mu)	USPAT; US-PGPUB	2003/06/23 15:07
4	414	(floating adj gate) WITH thickness near3 (angstrom nanometer micron nm .mu)	USPAT; US-PGPUB	2003/06/23 15:07
5	90	(floating adj gate) same ono WITH thickness near3 (angstrom nanometer micron nm .mu)	USPAT; US-PGPUB	2003/06/23 15:14
6	1	5859454.pn. and thickness near3 (angstrom nanometer micron nm .mu)	USPAT; US-PGPUB	2003/06/23 15:14
7	13	(Lam and Williams).in.	USPAT; US-PGPUB	2003/06/23 15:47
9	3	(Lam and chung).in. and troy	USPAT; US-PGPUB	2003/06/23 15:47
8	11	(Lam and chung).in. and ibm	USPAT; US-PGPUB	2003/06/23 15:47
10	14	((Lam and chung).in.) and nvram	USPAT; US-PGPUB	2003/06/23 15:47
11	162483	flash floating-gate floating adj gate eeprom non-volatile	USPAT	2003/06/23 15:48
12	301515	flash floating-gate floating adj gate eeprom non-volatile	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/23 15:48
13	29170	(depressed depression angular angled) near "4" floating-gate floating adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/23 15:49
14	37	(depressed depression angular angled) near4 (floating-gate floating adj gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/23 15:49
15	87	(Lam and chung).in.	USPAT; US-PGPUB	2003/06/23 15:49
16	1	((US-20010000112-\$.did.) and (ono oxide adj nitride)	US-PGPUB	2003/06/23 15:49